

## **FJP5021**

### High Voltage and High Reliability

- High Speed Switching :  $t_F = 0.1 \mu s$  (Typ.)
- Wide SOA



1.Base 2.Collector 3.Emitter

### **NPN Silicon Transistor**

### **Absolute Maximum Ratings** $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	800	V
V <sub>CEO</sub>	Collector-Emitter Voltage	500	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	٧
I <sub>C</sub>	Collector Current (DC)	5	Α
I <sub>CP</sub>	Collector Current (Pulse)	10	Α
I <sub>B</sub>	Base Current	2	Α
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	50	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

## **Electrical Characteristics** $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 1 \text{mA}, I_E = 0$	800			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_{C} = 5mA, I_{B} = 0$	500			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 1 \text{mA}, I_C = 0$	7			V
V <sub>CEX</sub> (sus)	Collector-Emitter Sustaining Voltage	$I_C = 2.5A$ , $I_{B1} = -I_{B2} = 1A$ L = 1mH, Clamped	500			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 500V, I_{E} = 0$			10	μА
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			10	μА
h <sub>FE1</sub>	DC Current Gain	$V_{CE} = 5V, I_{C} = 0.6A$	15		50	
h <sub>FE2</sub>		$V_{CE} = 5V$ , $I_C = 3A$	8			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_C = 3A, I_B = 0.6A$			1	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	$I_C = 3A, I_B = 0.6A$			1.5	V
C <sub>ob</sub>	Output Capacitance	$V_{CB} = 10V, I_{E} = 0, f=1MHz$		80		pF
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE} = 10V, I_{C} = 0.6A$		18		MHz
t <sub>ON</sub>	Turn On Time	V <sub>CC</sub> = 200V			0.5	μs
t <sub>STG</sub>	Storage Time	$I_C = 5I_{B1} = -2.5I_{B2} = 4A$			3	μs
t <sub>F</sub>	Fall Time	$R_L = 50\Omega$		0.1	0.3	μs

## **h**<sub>FE</sub> Classification

Classification	R	0	Y
h <sub>FE1</sub>	15 ~ 30	20 ~ 40	30 ~ 50

## **Typical Characteristics**

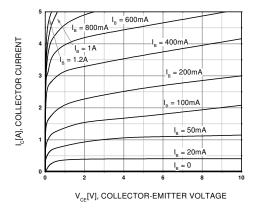


Figure 1. Static Characteristic

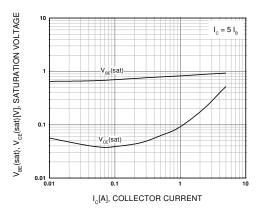


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

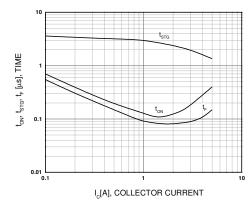


Figure 5. Switching Time

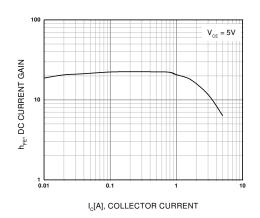


Figure 2. DC current Gain

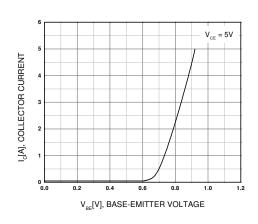


Figure 4. Base-Emitter On Voltage

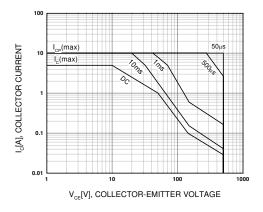


Figure 6. Forward Bias Safe Operating Area

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# Typical Characteristics (Continued)

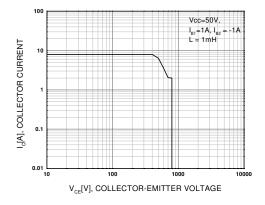


Figure 7. Reverse Bias Safe Operating Area

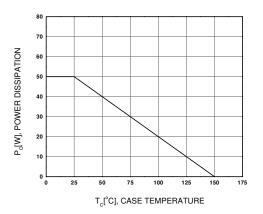
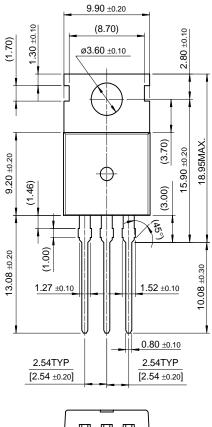
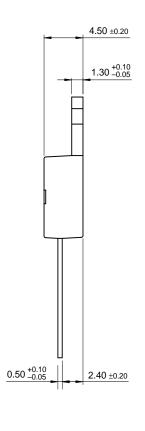


Figure 8. Power Derating

## **Package Dimensions**

## TO-220





10.00 ±0.20

Dimensions in Millimeters

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E <sup>2</sup> CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	I <sup>2</sup> C™	OCX <sup>TM</sup>	RapidConfigure™	UHC™
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Rev. I2

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